Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC6026MFV

General-Purpose Amplifier Applications

• High voltage and high current

: V_{CEO} = 50 V, I_C = 150 mA (max)

• Excellent hFE linearity :

 $h_{FE} (I_C = 0.1 \text{ mA})/h_{FE} (I_C = 2 \text{ mA}) = 0.95 \text{ (typ.)}$

• High h_{FE} : h_{FE} = 120~400

• Complementary to 2SA2154MFV

• Lead (Pb) - free

Maximum Ratings (Ta = 25°C)

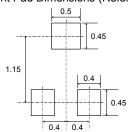
Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	٧
Emitter-base voltage	V _{EBO}	5	٧
Collector current	I _C	150	mA
Base current	I _B	30	mA
Collector power dissipation	P _C	150*	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

^{*:} Mounted on FR4 board (25.4 mm × 25.4 mm × 1.6mm)

1.8ASE VESM 2.EMITTER 3.COLLECTOR JEDEC JEITA TOSHIBA 2-1L1A

Weight: 0.0015 g (typ.)

Mount Pad Dimensions (Reference)



Unit: mm

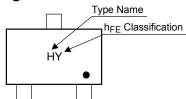
Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current	I _{CBO}	$V_{CB} = 60 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cutoff current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μА
DC current gain	h _{FE} (Note)	$V_{CE} = 6 \text{ V}, I_{C} = 2 \text{ mA}$	120	_	400	_
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$	_	0.1	0.25	V
Transition frequency	f _T	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$	60	_	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	0.95	3	pF

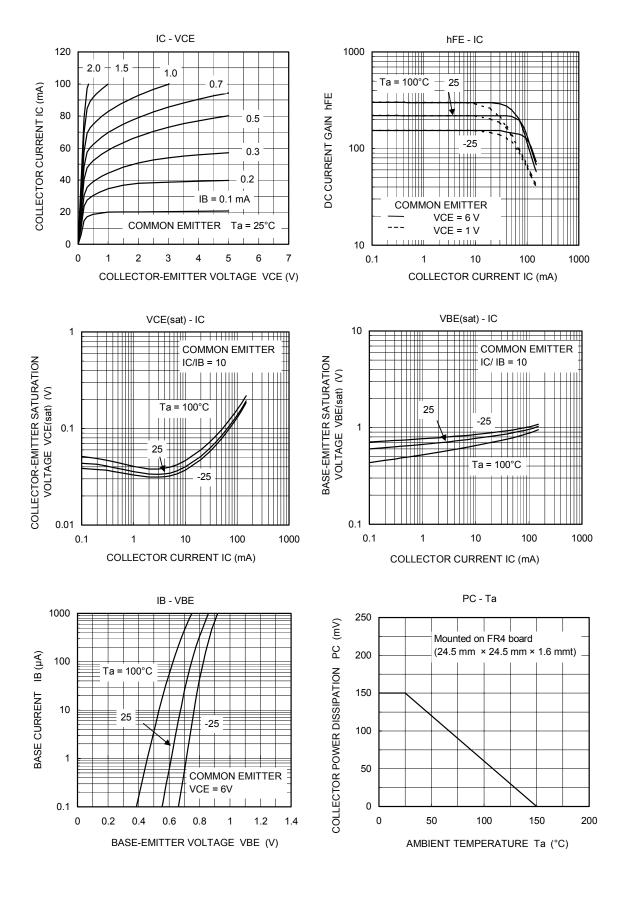
Note: hFE classification Y (Y): 120~240, GR (G): 200~400

() marking symbol

Marking



2



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